CHENMKO ENTERPRISE CO.,LTD

CHEMD12PT

Lead free devices

SURFACE MOUNT
Dual Digital Silicon Transistor

VOLTAGE 50 Volts CURRENT 30 mAmpere

APPLICATION

* Switching circuit, Inverter, Interface circuit, Driver circuit.

FEATURE

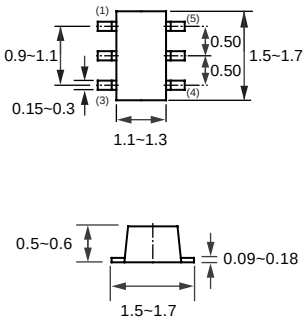
* Small surface mounting type. (SOT-563)
* High current gain.
* Suitable for high packing density.
* Low colloector-emitter saturation.
* High saturation current capability.
* Both the CHDTA144E & CHDTC144E in one package.
* Built in bias resistor(R1=47kΩ, Typ.)

MARKING

* BX



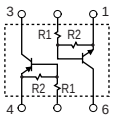
SOT-563



Dimensions in millimeters

SOT-563

CIRCUIT



CHDTA144E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	Supply voltage		–	-50	V
V_{IN}	Input voltage		-40	+10	V
I_O	DC Output current		–	-30	mA
$I_{C(Max.)}$			–	-100	
P_{TOT}	Total power dissipation	$T_{amb} \leq 25\ ^{\circ}C$, Note 1	–	150	mW
T_{STG}	Storage temperature		–55	+150	°C
T_J	Junction temperature		–	150	°C
$R\theta_{J\text{-}S}$	Thermal resistance	junction - soldering point	–	140	°C/W

Note

Transistor mounted on an FR4 printed-circuit board.

CHDTC144E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	Supply voltage		–	50	V
V_{IN}	Input voltage		-10	+40	V
I_O	DC Output current		–	30	mA
$I_{C(Max.)}$			–	100	
P_{TOT}	Total power dissipation	$T_{amb} \leq 25\ ^{o}C$, Note 1	–	150	mW
T_{STG}	Storage temperature		–55	+150	^{o}C
T_J	Junction temperature		–	150	^{o}C
$R\theta_{J-S}$	Thermal resistance	junction - soldering point	–	150	$^{o}C/W$

Note

Transistor mounted on an FR4 printed-circuit board.

CHDTA144E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise speciÞed.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{Ioff)}$	Input off voltage	I_O=-100uA; V_{CC}=-5.0V	-0.5	–	–	V
$V_{I(on)}$	Input on voltage	I_O=-2mA; V_O=-0.3V	–	–	-3.0	V
$V_{O(on)}$	Output voltage	I_O=-10mA; I_I=-0.5mA	–	–	-0.3	V
I_I	Input current	V_I=-5V	–	–	-0.18	mA
$I_{C(off)}$	Output current	V_I=0V; V_{CC}=-50V	–	–	-0.5	uA
h_{FE}	DC current gain	I_O=-5mA; V_O=-5.0V	68	–	–	
R_1	Input resistor		32.9	47.0	61.1	KΩ
R_2/R_1	Resistor ratio		0.8	1.0	1.2	
f_T	Transition frequency	I_C=-5mA, V_{CE}=-10.0V f=100MHz	–	250	–	MHz

Note

Pulse test: tp≤300uS; δ≤0.02.

CHDTC144E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise speciÞed.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{Ioff)}$	Input off voltage	I_O=100uA; V_{CC}=5.0V	0.5	–	–	V
$V_{I(on)}$	Input on voltage	I_O=2mA; V_O=0.3V	–	–	3.0	V
$V_{O(on)}$	Output voltage	I_O=10mA; I_I=0.5mA	–	–	0.3	V
I_I	Input current	V_I=5V	–	–	0.18	mA
$I_{C(off)}$	Output current	V_I=0V; V_{CC}=50V	–	–	0.5	uA
h_{FE}	DC current gain	I_O=5mA; V_O=5.0V	68	–	–	
R_1	Input resistor		32.9	47	61.1	KΩ
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Note

Pulse test: tp≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHEMD12PT)

CHDTA144E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current (ON characteristics)

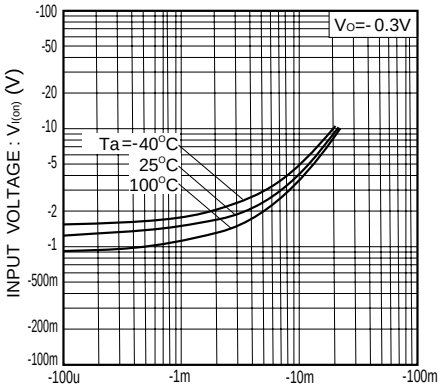


Fig.2 Output current vs. input voltage (OFF characteristics)

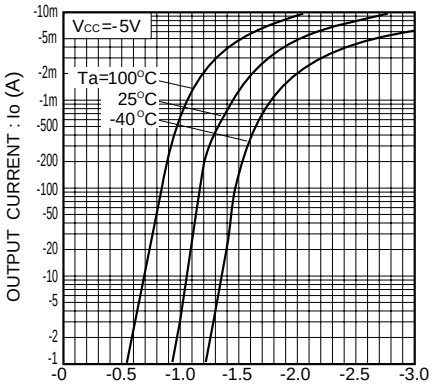


Fig.3 DC current gain vs. output current

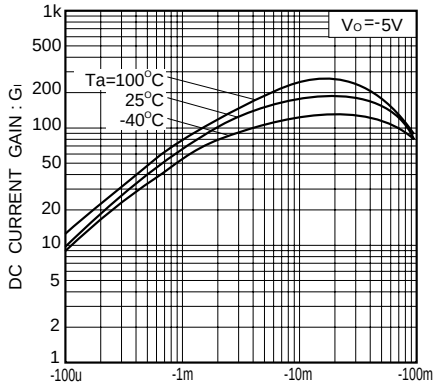
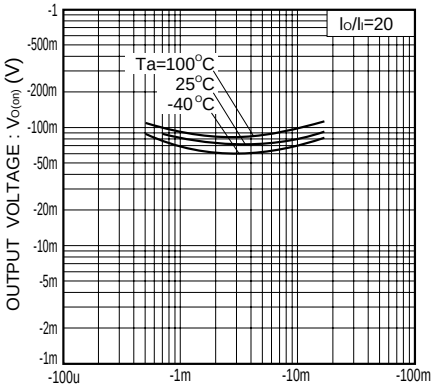


Fig.4 Output voltage vs. output current



RATING CHARACTERISTIC CURVES (CHEMD12PT)

CHDTC144E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current (ON characteristics)

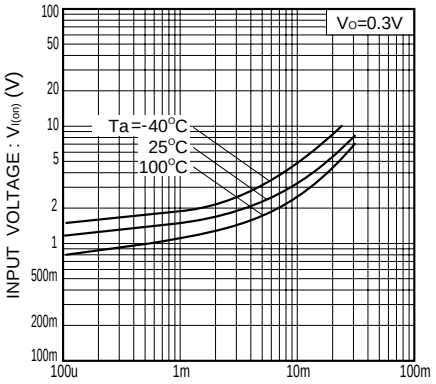


Fig.2 Output current vs. input voltage (OFF characteristics)

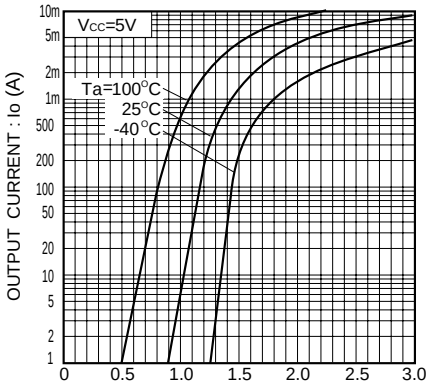


Fig.3 DC current gain vs. output current

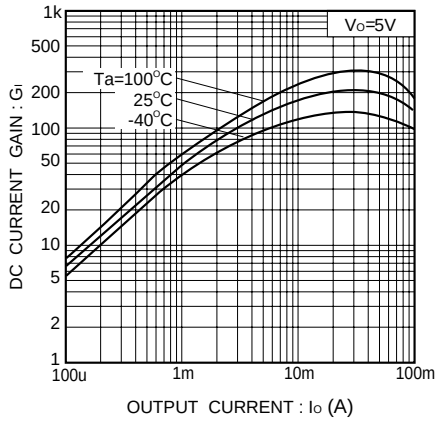


Fig.4 Output voltage vs. output current

